Compare FIB products NX5000, NX9000, NX2000

Model		Focused Ion and Electron Beam System Ethos NX5000	Real-time 3D analytical FIB-SEM NX9000	Focused Ion and Electron Beam System & Triple Beam System NX2000
SEM	Electron source	Cold cathode field emission source	Cold cathode field emission source	Cold cathode field emission source
	Accelerating voltage	0.1 - 30 kV	0.1 - 30 kV	0.5 kV - 30 kV
	Resolution	1.5 nm @ 1 kV, 0.7 nm @ 15 kV	2.1 nm@1 kV, 1.6 nm@15 kV	2.8 nm @5 kV, 3.5 nm @1 kV
FIB	Ion source	Ga liquid metal ion source	Ga liquid metal ion source	Ga liquid metal ion source
	Accelerating voltage	0.5 - 30 kV	0.5 - 30 kV	0.5 kV - 30 kV
	Resolution	4 nm @ 30 kV, 60 nm @ 2 kV (Edge resolution)	4.0 nm@30 kV	4 nm @30 kV, 60 nm @2 kV
	Maximum beam current	100 nA	100 nA	100 nA
Low energy ion beam			Ar*	Ar*/Xe*
Sample stage traverse		X: 155 mm Y: 155 mm Z: 16.5 mm R: 0 - 360° T: -10 - 59°	X: 0 - 20 mm Y: 0 - 20 mm Z: 0 - 20 mm R: 0 - 360° T: -25 - 45°	X: 0 - 205 mm Y: 0 - 205 mm Z: 0 - 10 mm R: 0 - 360° T: -5 - 60°
Maximum sample size		150 mm in diameter	6 mm x 6 mm, 2 mm thick	200 mm in diameter
Signal detector		In-column SE(U) In-column BSE(U) In-column BSE(L) Chamber Port SE(L)	In-column SED In-column BSED Chamber SED BSE detector* TE detector*	Upper/Lower SED & BSED
Analysis system		Energy Dispersive X-ray Spectroscopy (EDS)* Electron Backscatter Diffraction(EBSD)*	Energy Dispersive X-ray Spectroscopy (EDS)* Electron Backscatter Diffraction(EBSD)*	Energy Dispersive X-ray Spectroscopy (EDS)*

*option

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